

## IN THE CLAIMS

Per the revised amendment practice, a complete listing of all claims in the application follows.

Claims 1-58 (Cancelled).

59. (Original) A method of forming oxide over a transistor gate and over a substrate extending laterally from under said gate, said method comprising:

- forming an undoped first oxide over said gate and said substrate;
- forming an undoped second oxide over said first oxide;
- doping said second oxide after forming said second oxide;
- depositing insulation over said second oxide after doping said second oxide;
- initiating a removal of a portion of said insulation; and
- stopping said removal with said second oxide.

60. (Original) The method in claim 59, wherein said step of forming an undoped first oxide comprises forming a TEOS-based oxide.

61. (Original) The method in claim 59, wherein said step of forming an undoped first oxide comprises forming a continuous silicon dioxide layer.

62. (Original) The method in claim 59, wherein said step of forming an undoped first oxide comprises forming a first oxide that is thicker over said gate than lateral to said gate, and wherein said first oxide is thicker over said substrate than lateral to said gate.

63. (Original) The method in claim 62, wherein said step of forming an undoped first oxide comprises forming a non-porous first oxide.

64. (Original) The method in claim 62, wherein said step of forming an undoped second oxide comprises forming a second oxide that is thicker over said gate than lateral to said gate, and wherein said second oxide is thicker over said substrate than lateral to said gate.

65. (Original) The method of claim 64, wherein said step of forming an undoped second oxide comprises:

- depositing 500 to 1000 Angstroms of said second oxide over said gate;
- depositing 500 to 1000 Angstroms of said second oxide over said substrate; and
- depositing 0 to 50 Angstroms of said second oxide lateral to said gate.

Claims 66-88 (Cancelled).